# 2SA1029, 2SA1030

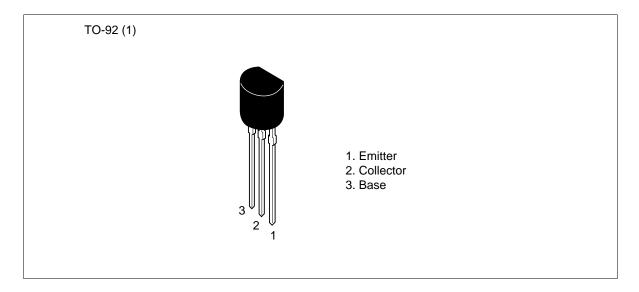
Silicon PNP Epitaxial

# **HITACHI**

### **Application**

- Low frequency amplifier
- Complementary pair with 2SC458 and 2SC2308

#### **Outline**





### 2SA1029, 2SA1030

### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	2SA1029	2SA1030	Unit
Collector to base voltage	$V_{CBO}$	-30	<b>–</b> 55	V
Collector to emitter voltage	$V_{\text{CEO}}$	-30	<b>-</b> 50	V
Emitter to base voltage	$V_{EBO}$	<b>-</b> 5	<b>–</b> 5	V
Collector current	I <sub>c</sub>	-100	-100	mA
Emitter current	I <sub>E</sub>	100	100	mA
Collector power dissipation	P <sub>c</sub>	300	300	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

#### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

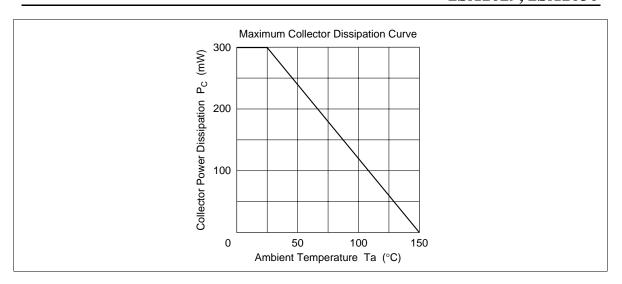
		2SA1	2SA1029 2SA1030						
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-30	_	_	-55	_	_	V	$I_{c} = -10 \ \mu\text{A}, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-30	_	_	-50	_	_	V	$I_{C} = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	<b>–</b> 5	_	_	<b>-</b> 5	_	_	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	-0.5	_	_	-0.5	μΑ	$V_{CB} = -18 \text{ V}, I_{E} = 0$
Emitter cutoff current	I <sub>EBO</sub>	_	_	-0.5	_	_	-0.5	μΑ	$V_{EB} = -2 \text{ V}, I_{C} = 0$
DC current trnsfer ratio	h <sub>FE</sub> *1	100	_	500	100	_	320		$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Base to emitter voltage	$V_{BE}$	_	_	-0.8	_	_	-0.8	V	$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	-0.2	_	_	-0.2	V	$I_{\rm C} = -10 \text{ mA},$ $I_{\rm B} = -1 \text{ mA}$
Gain bandwidth product	f <sub>T</sub>	200	280	_	200	280	_	MHz	$V_{CB} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Collector output capacitance	Cob	_	3.3	4.0	_	3.3	4.0	pF	$V_{CB} = -10 \text{ V}, I_{E} = 0,$ f = 1 MHz

Note: 1. The 2SA1029 and 2SA1030 are grouped by  $h_{FE}$  as follows.

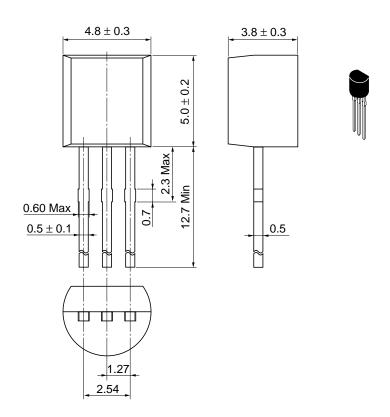
	В	C	ט
2SA1029	100 to 200	160 to 320	250 to 500
2SA1030	100 to 200	160 to 320	_

See characteristic curves of 2SA1031 and 2SA1032.

## 2SA1029, 2SA1030



Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

#### **Cautions**

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